Product Summary

$V_{(BR)DSS}$	$R_{DS(ON)}$ max	I_D max T_A = +25°C
100V	122mΩ @ V_{GS} = 10V	2.9A
	133mΩ @ V_{GS} = 4.5V	2.7A

Description

This MOSFET has been designed to minimize the on-state resistance ($R_{DS(on)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- Backlighting
- Power Management Functions
- DC-DC Converters

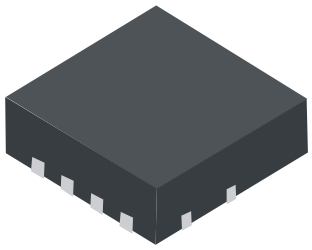
Features

- 100% Unclamped Inductive Switch (UIS) test in production
- Low $R_{DS(ON)}$ – ensures on state losses are minimized
- Small form factor thermally efficient package enables higher density end products
- Occupies just 33% of the board area occupied by SO-8 enabling smaller end product
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

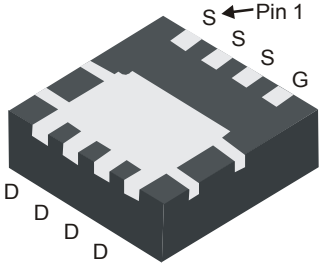
Mechanical Data

- Case: POWERDI3333
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See diagram
- Terminals: Finish — Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208 e3
- Weight: 0.034 grams (approximate)

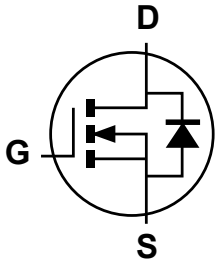
POWERDI3333



Top View



Bottom View



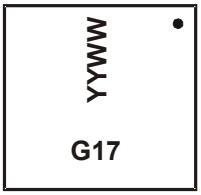
Equivalent Circuit

Ordering Information (Note 4)

Part Number	Compliance	Case	Packaging
DMN10H170SFG-7	Standard	POWERDI3333	2000/Tape & Reel
DMN10H170SFG-13	Standard	POWERDI3333	3000/Tape & Reel

Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



G17 = Product marking code
YYWW = Date code marking
YY = Last digit of year (ex: 10 for 2010)
WW = Week code (01 – 53)

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V_{DSS}	100	V
Gate-Source Voltage			V_{GSS}	±20	V
Continuous Drain Current (Note 6) V_{GS} = 10V	Steady State	T_A = +25°C T_A = +70°C T_C = +25°C	I_D	2.9 2.4 8.5	A
	t<10s	T_A = +25°C T_A = +70°C	I_D	3.7 3.0	A
Maximum Continuous Body Diode Forward Current (Note 6)			I_S	3.0	A
Pulsed Drain Current (10µs pulse, duty cycle = 1%)			I_{DM}	16	A
Avalanche Current (Note 7)			I_{AR}	5.3	A
Avalanche Energy (Note 7)			E_{AR}	20	mJ

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 5)	T_A = +25°C	P_D	0.94	W
	T_A = +70°C		0.6	
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	137	°C/W
	t<10s		82	°C/W
Total Power Dissipation (Note 6)	T_A = +25°C	P_D	2.0	W
	T_A = +70°C		1.3	
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{\theta JA}$	60	°C/W
	t<10s		36	°C/W
Thermal Resistance, Junction to Case (Note 6)		$R_{\theta JC}$	7.0	°C/W
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV_{DSS}	100	—	—	V	V_{GS} = 0V, I_D = 250µA
Zero Gate Voltage Drain Current	I_{DSS}	—	—	1.0	µA	V_{DS} = 100V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	±100	nA	V_{GS} = ±20V, V_{DS} = 0V
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	$V_{GS(th)}$	1.0	—	3.0	V	V_{DS} = V_{GS}, I_D = 250µA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	99	122	mΩ	V_{GS} = 10V, I_D = 3.3A
		—	104	133		V_{GS} = 4.5V, I_D = 3.0A
Forward Transfer Admittance	$\|Y_{fs}\|$	—	4.4	—	S	V_{DS} = 10V, I_D = 3.3A
Diode Forward Voltage	V_{SD}	—	0.7	1.0	V	V_{GS} = 0V, I_S = 3.3A
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C_{iss}	—	870.7	—	pF	V_{DS} = 25V, V_{GS} = 0V, f = 1.0MHz
Output Capacitance	C_{oss}	—	40.8	—	pF	
Reverse Transfer Capacitance	C_{rss}	—	24.6	—	pF	
Gate resistance	R_g	—	1.1	—	Ω	V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz
Total Gate Charge (V_{GS} = 4.5V)	Q_g	—	7.0	—	nC	V_{DS} = 50V, I_D = 3.3A
Total Gate Charge (V_{GS} = 10V)	Q_g	—	14.9	—	nC	
Gate-Source Charge	Q_{gs}	—	3.3	—	nC	
Gate-Drain Charge	Q_{gd}	—	3.0	—	nC	
Turn-On Delay Time	$t_{D(on)}$	—	4.4	—	ns	V_{DD} = 50V, V_{GEN} = 10V, R_{GEN} = 6.0Ω, I_D = 3.3A
Turn-On Rise Time	t_r	—	2.3	—	ns	
Turn-Off Delay Time	$t_{D(off)}$	—	13.9	—	ns	
Turn-Off Fall Time	t_f	—	3.4	—	ns	
Reverse Recovery Time	t_{rr}	—	22.4	—	ns	I_S = 3.3A, dI/dt = 100A/µs
Reverse Recovery Charge	Q_{rr}	—	19.7	—	nC	

Notes:
5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
7. UIS in production with L = 1.43mH, T_J = +25°C.
8. Short duration pulse test used to minimize self-heating effect.
9. Guaranteed by design. Not subject to product testing.

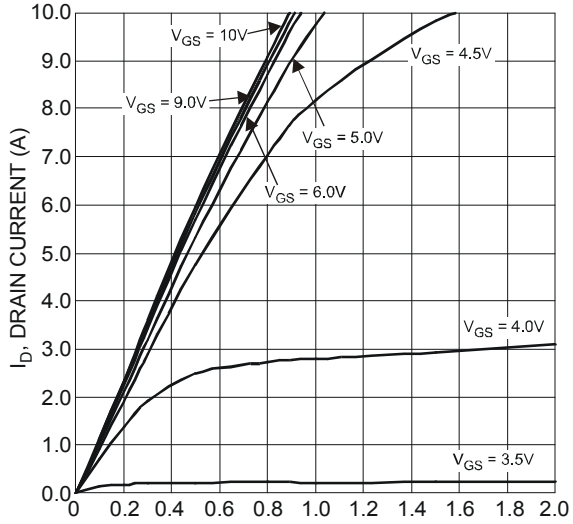


Figure 1 Typical Output Characteristic

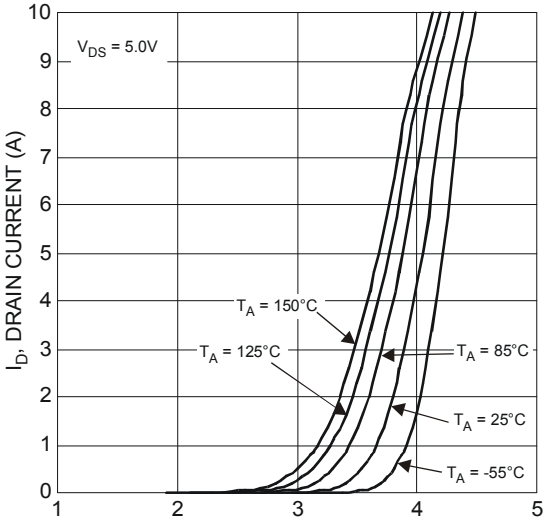


Figure 2 Typical Transfer Characteristics

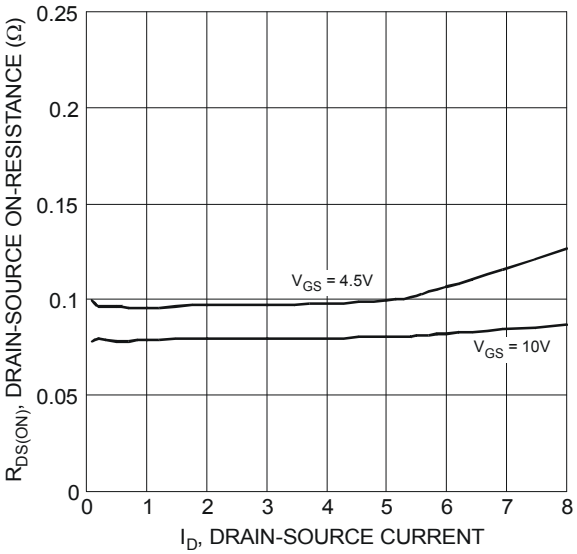


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

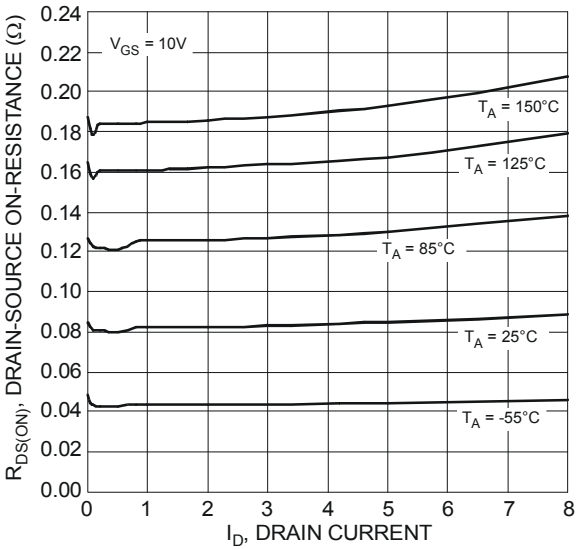


Figure 4 Typical On-Resistance vs. Drain Current and Temperature

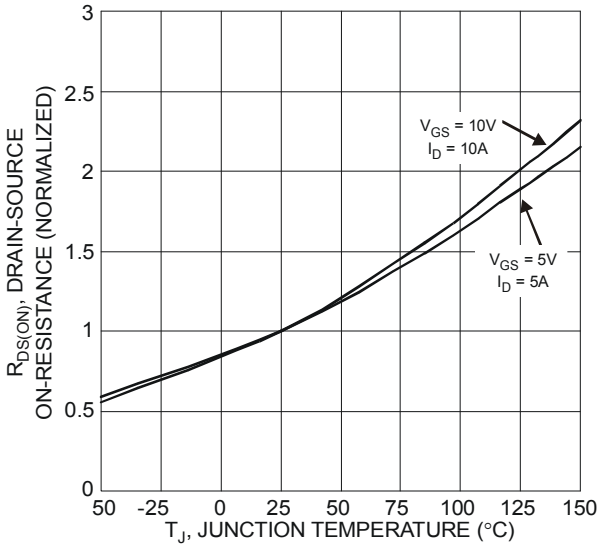


Figure 5 On-Resistance Variation with Temperature

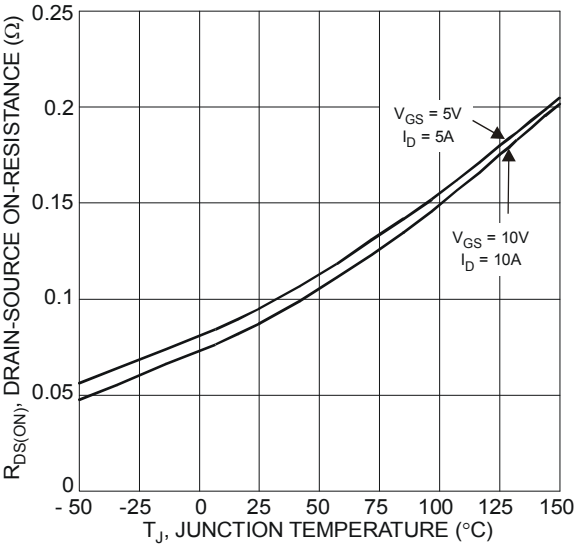


Figure 6 On-Resistance Variation with Temperature

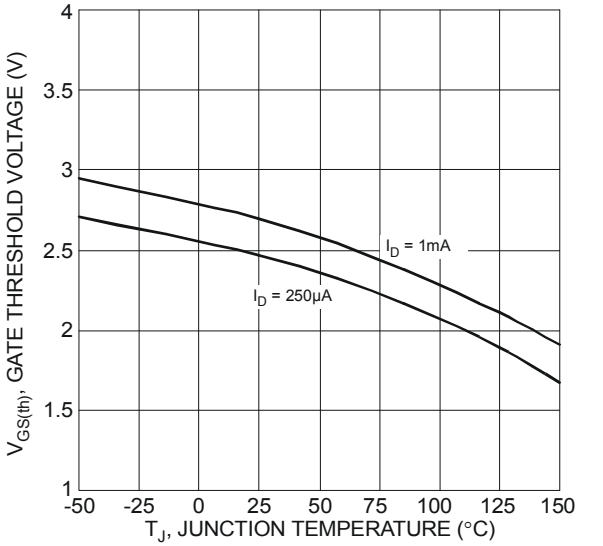


Figure 7 Gate Threshold Variation vs. Ambient Temperature

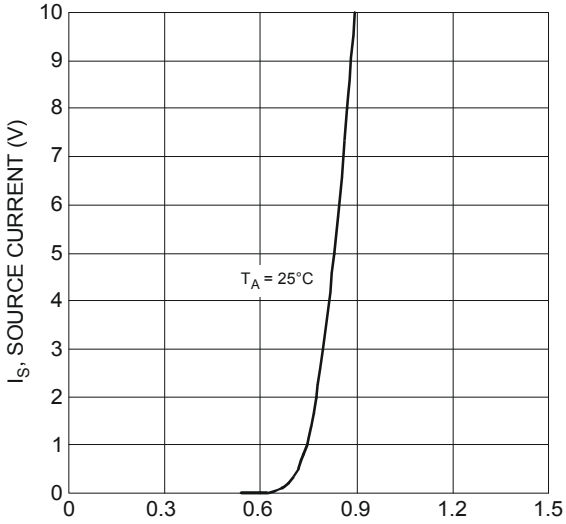


Figure 8 Diode Forward Voltage vs. Current

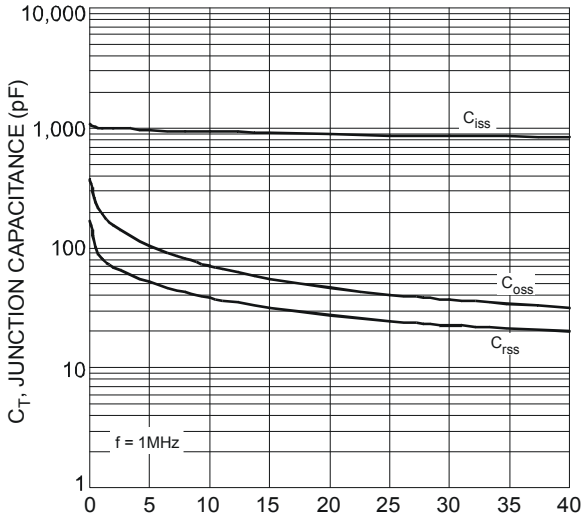


Figure 9 Typical Junction Capacitance

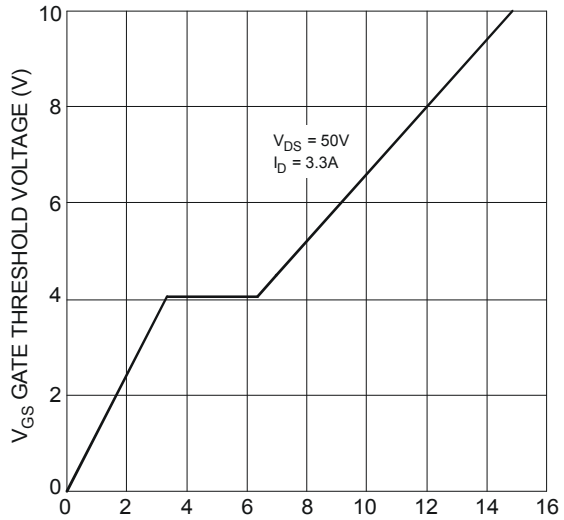


Figure 10 Gate Charge

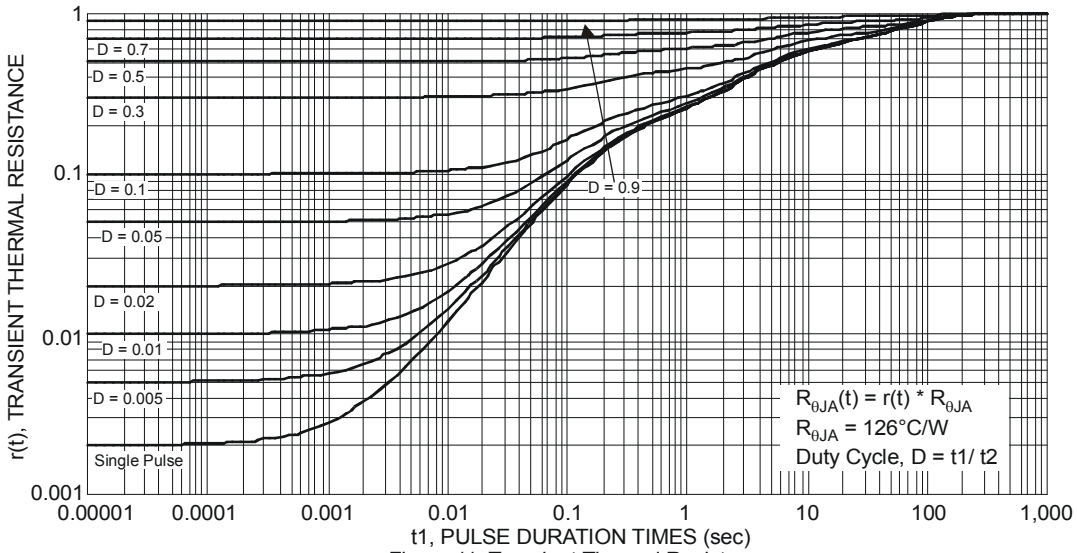
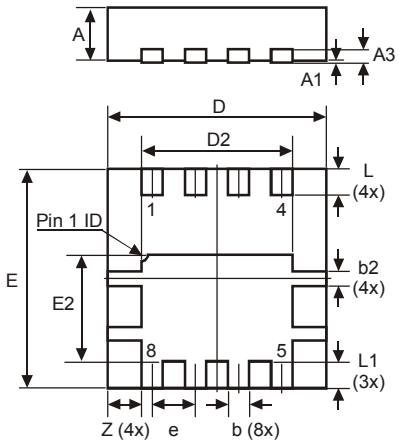


Figure 11 Transient Thermal Resistance

Package Outline Dimensions

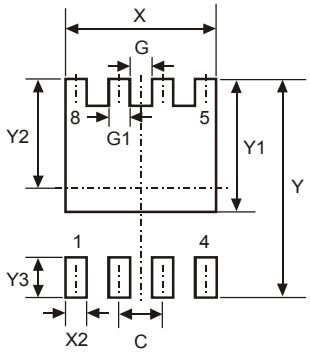
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



POWERDI3333-8			
Dim	**Min**	**Max**	**Typ**
D	3.25	3.35	3.30
E	3.25	3.35	3.30
D2	2.22	2.32	2.27
E2	1.56	1.66	1.61
A	0.75	0.85	0.80
A1	0	0.05	0.02
A3	–	–	0.203
b	0.27	0.37	0.32
b2	–	–	0.20
L	0.35	0.45	0.40
L1	–	–	0.39
e	–	–	0.65
Z	–	–	0.515
All Dimensions in mm			

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
C	0.650
G	0.230
G1	0.420
Y	3.700
Y1	2.250
Y2	1.850
Y3	0.700
X	2.370
X2	0.420

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